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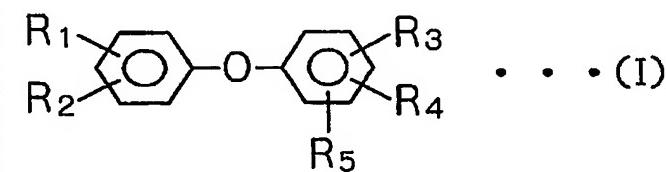
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(54) Title: DEVELOPER COMPOSITION FOR RESISTS AND METHOD FOR FORMATION OF RESIST PATTERN



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of R<sub>1</sub> and R<sub>2</sub> represents an alkyl or alkoxy group having 5 to 18 carbon atoms and any reminder member represents a hydrogen atom, or an alkyl or alkoxy group having 5 to 18 carbon atoms, and at least one member of R<sub>3</sub>, R<sub>4</sub> and R<sub>5</sub> represents a group represented by the general formula (II), wherein M represents a metal atom, and any reminder member represents a hydrogen atom or a group represented by the general formula (II).

(57) Abstract: A developer composition for resists which has a high dissolution rate (high developing sensitivity). The developer composition for resists is a developer composition for resists, comprising an organic quaternary ammonium base as a main component and a surfactant, said surfactant containing an anionic surfactant represented by the following general formula (I), wherein at least one member

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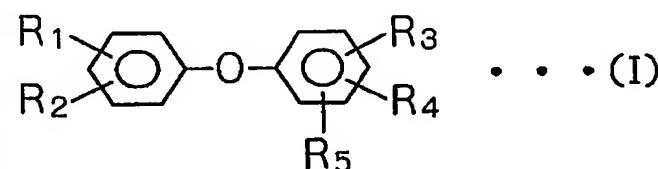
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